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Quad. 2-input AND Gates

RENESAS

ADE-205-250A (Z)

2nd. Edition Jul. 2001

Description

The HD74LV08A has four two-input AND gates in a 14-pin package.

Low-voltage and high-speed operation is suitable for the battery-powered products (e.g., notebook computers), and the low-power consumption extends the battery life.

Features

- $V_{cc} = 2.0 \text{ V}$ to 5.5 V operation
- All inputs V_{IH} (Max.) = 5.5 V (@V_{cc} = 0 V to 5.5 V)
- All outputs V_0 (Max.) = 5.5 V (@V_{cc} = 0 V)
- Typical V_{oL} ground bounce < 0.8 V (@V_{cc} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.3 V (@V_{CC} = 3.3 V, Ta = 25°C)
- Output current $\pm 6 \text{ mA}$ (@V_{cc} = 3.0 V to 3.6 V), $\pm 12 \text{ mA}$ (@V_{cc} = 4.5 V to 5.5 V)

Function Table

Inputs

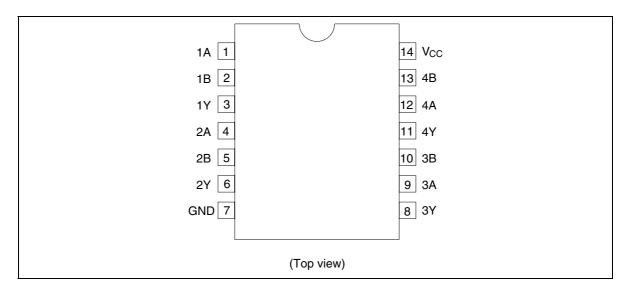
Α	В	Output Y
Н	Н	Н
L	X	L
Х	L	L

Note: H: High level

L: Low level

X: Immaterial

Pin Arrangement





Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range*1	V	-0.5 to 7.0	V	
Output voltage range*1,2	V _o	–0.5 to V $_{\rm cc}$ + 0.5	V	Output: H or L
		-0.5 to 7.0	-	V _{cc} : OFF
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	I _{ок}	±50	mA	V_{o} < 0 or V_{o} > V_{cc}
Continuous output current	I _o	±25	mA	$V_o = 0$ to V_{cc}
Continuous current through V_{cc} or GND	$I_{\rm cc}$ or $I_{\rm gnd}$	±50	mA	
Maximum power dissipation at Ta = 25°C (in still air)* ³	P _T	785	mW	SOP
		500	-	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This value is limited to 5.5 V maximum.

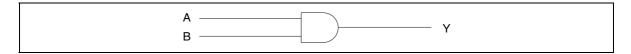
3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Item	Symbol	Min	Мах	Unit	Conditions
Supply voltage range	V _{cc}	2.0	5.5	V	
Input voltage range	V	0	5.5	V	
Output voltage range	Vo	0	V _{cc}	V	
Output current	I _{он}	_	-50	μA	$V_{cc} = 2.0 V$
		_	-2	mA	V_{cc} = 2.3 to 2.7 V
		_	-6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	-12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
	I _{ol}	_	50	μA	$V_{cc} = 2.0 V$
		_	2	mA	V_{cc} = 2.3 to 2.7 V
		_	6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Input transition rise or fall rate	$\Delta t / \Delta v$	0	200	ns/V	V_{cc} = 2.3 to 2.7 V
		0	100		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		0	20		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	Та	-40	85	°C	

Recommended Operating Conditions

Note: Unused or floating inputs must be held high or low.

Logic Diagram



DC Electrical Characteristics

Ta = -40 to $85^{\circ}C$

Item	Symbol	V _{cc} (V)*	Min	Тур	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.0	1.5	_	_	V	
		2.3 to 2.7	$V_{cc} imes 0.7$	_	—	_	
		3.0 to 3.6	$V_{cc} imes 0.7$	_	_	_	
		4.5 to 5.5	$V_{cc} imes 0.7$	_	_	_	
	V _{IL}	2.0	_	_	0.5	_	
		2.3 to 2.7	_	_	$V_{cc} imes 0.3$	_	
		3.0 to 3.6	_	_	$V_{cc} imes 0.3$	_	
		4.5 to 5.5	_	—	$V_{cc} imes 0.3$	_	
Output voltage	V _{OH}	Min to Max	$V_{cc} - 0.1$	—	_	V	Ι _{οн} = –50 μΑ
		2.3	2.0	_	_	_	$I_{OH} = -2 \text{ mA}$
		3.0	2.48	_	_	_	I _{он} =6 mA
		4.5	3.8	_	_	_	I _{OH} = -12 mA
	V _{ol}	Min to Max	_	—	0.1	_	$I_{oL} = 50 \ \mu A$
		2.3	_	_	0.4	_	$I_{oL} = 2 \text{ mA}$
		3.0	_	_	0.44	_	$I_{oL} = 6 \text{ mA}$
		4.5	_	_	0.55	_	I _{oL} = 12 mA
Input current	I _{IN}	0 to 5.5	_	_	±1	μA	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent supply current	I _{cc}	5.5	_	—	20	μA	$V_{\rm IN} = V_{\rm cc}$ or GND, $I_{\rm o} = 0$
Output leakage current	I _{OFF}	0	_	_	5	μA	$V_{_{\rm I}}$ or $V_{_{\rm O}}$ = 0 V to 5.5 V
Input capacitance	C _{IN}	3.3	_	3.3	—	pF	$V_{I} = V_{cc}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

 $V_{cc} = 2.5 \pm 0.2 \text{ V}$

		Ta =	25°C		Ta = -40 to 85°C					
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Propa- gation delay time	t _{PLH} t _{PHL}		7.9	13.8	1.0	16.0	ns	С _L = 15 рF	A or B	Y
		—	10.5	17.3	1.0	20.0	_	C _∟ = 50 pF		

 $V_{cc} = 3.3 \pm 0.3 \text{ V}$

		Ta =	25°C		Ta = -40 to 85°C					
Item	Symbol	Min	Тур	Max	Min	Мах	Unit	Test Conditions	FROM (Input)	TO (Output)
Propa- gation delay time	t _{PLH} t _{PHL}		5.6	8.8	1.0	10.5	ns	С _L = 15 рF	A or B	Y
		_	7.5	12.3	1.0	14.0	-	C _∟ = 50 pF		

 $V_{cc} = 5.0 \pm 0.5 \text{ V}$

		Ta =	25°C Ta = -40		Ta = 25°C Ta =			Ta = -40 to 85°C				
Item	Symbol	Min	Тур	Max	Min	Мах	Unit	Test Conditions	FROM (Input)	TO (Output)		
Propa- gation delay time	t _{plH} t _{pHL}	_	4.1	5.9	1.0	7.0	ns	С _L = 15 рF	A or B	Y		
		_	5.5	7.9	1.0	9.0	-	C _L = 50 pF				

Operating Characteristics

 $C_{L} = 50 \text{ pF}$

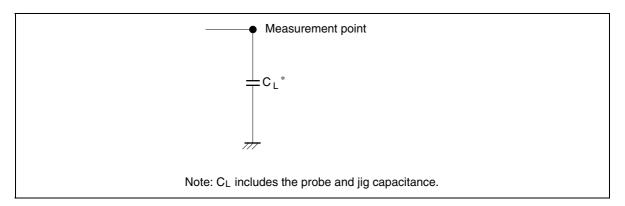
			Ta = 25°	°C			
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Power dissipation capacitance	$C_{_{PD}}$	3.3	_	8.0	_	pF	f = 10 MHz
		5.0	_	10.0	_		

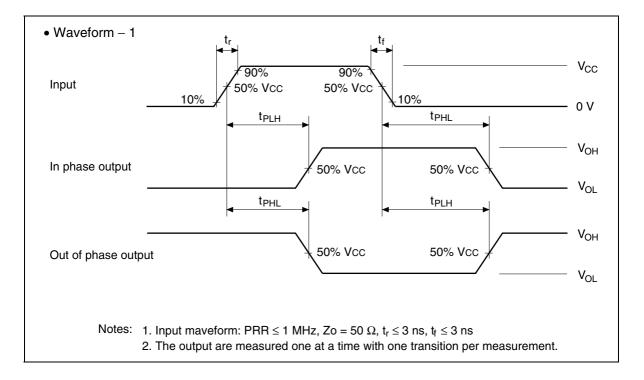
Noise Characteristics

 $C_{L} = 50 \text{ pF}$

			Ta = 25°	°C			
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Quiet output, maximum dynamic V _{oL}	$V_{\text{OL}(P)}$	3.3	_	0.2	0.8	V	
Quiet output, minimum dynamic V _{oL}	$V_{OL(V)}$	3.3	—	-0.1	-0.8		
Quiet output, minimum dynamic V _{он}	$V_{OH(V)}$	3.3	_	3.1	_		
High-level dynamic input voltage	$V_{\text{IH (D)}}$	3.3	2.31	_	_	V	
Low-level dynamic inout voltage	$V_{\text{IL (D)}}$	3.3			0.99		

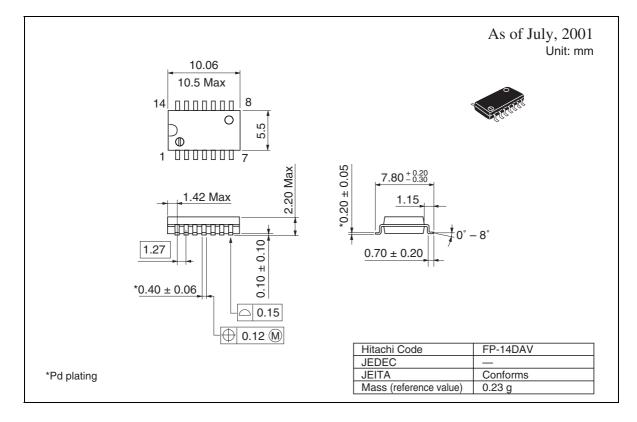
Test Circuit



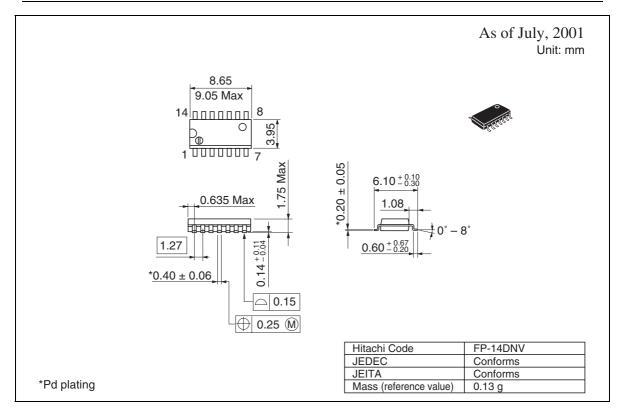


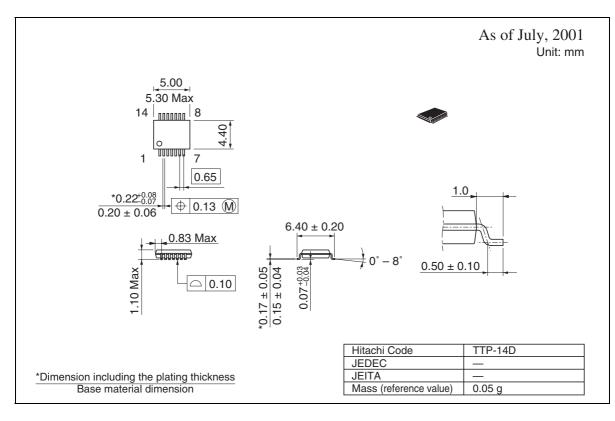
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Package Dimensions









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